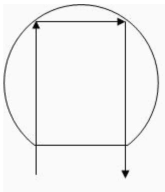
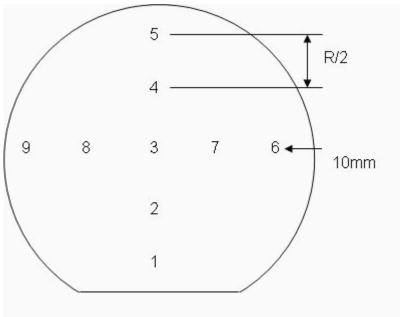
Icemos Technology Ltd **Product Specification** **1003.723401** Issue Date 17 April 2024 16:26:1

Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Length	NONE	Wafer Vendor
	5.0	Overall Thickness	400.00 +/- 5.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	7.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	None	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Front Surface Quality	Polished. No frontside scratches. No orange peel, edge chips or other surface defects.	Bright Light, 100% (note 2)
	12.0	Backsurface condition	Polished with light handling marks	Bright Light, 100% (note2)
	13.0	Frontside final oxide thickness	22,000.00 +/- 1,100.00 A	Nanospec centre point, 4%
	14.0	Lasermarking	Laser Scribe on backside. IceMOS Standard format: YYMM-XXXXX	
	15.0	Backside Laser Marking Location	Left Hand Side of Wafer Flat	
	16.0	Edge Rounding	Edge profile to suit 400um handle with edge grind.	IceMOS Internal - Edge profile to suit 400um handle with edge grind.
HandleSilicon	17.0	Handle Silicon Raw Material	Prime Silicon	
	18.0	Handle Growth Method	CZ	Wafer Vendor
	19.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	20.0	Handle Thickness	400.00 +/- 5.00 µm	ADE, 100%
	21.0	Handle Doping Type	P	Wafer Vendor
	22.0	Handle Dopant	Boron	Wafer Vendor
	23.0	Handle Resistivity	1 ~ 10 Ohmcm	Wafer Vendor
	24.0	Handle Oxygen Concentration	<15ppma ASTM-83; new	Wafer vendor
	25.0	Backside Finish	Polished, with lasermarking. Light handling scrtaches.	Guaranteed by process
	26.0	Surface Haze	none	Bright Light, 100% (note 2)

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below: 		
Additional Information			